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# Impact of surface passivation of III-V elements on Si (001) substrate based on absolute surface and barrier energy calculations

Sreejith Pallikkara Chandrasekharan, Divishth Gutpa, Laurent Pedesseau,  
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# Impact of surface passivation of III-V elements on Si (001) substrate based on absolute surface and barrier energy calculations



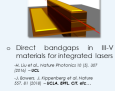
Sreejith Pallikkara Chandrasekharan<sup>1,\*</sup>, Divishth Gupta<sup>1</sup>, Laurent Pedesseau<sup>1</sup>, Charles Cornet<sup>1</sup>

(1) Univ Rennes, INSA Rennes, CNRS, Institut FOTON-UMR 6082, F-35000, Rennes, France.

## Introduction

Integrating III-V compound semiconductors on (001) Si substrates is a long-standing challenge, which has driven many researches for the past 40 years. A large portfolio of passive photonic devices and their mature fabrication technology are available on the Si platform. This gives greater flexibility to design photonics integrated circuits (PICs) as compared to the pure III-V technologies and opens a number of possibilities for e.g. lasers, photovoltaic energy production, or energy storage via solar hydrogen production.

## Active photonics



Direct bandgap III-V materials for integrated lasers

## Electronics



High carrier mobilities in III-V materials for advanced CMOS concepts

## Passive photonics



Non-linear properties of III-V materials for integrated passive devices (frequency converters)

## Water splitting



High efficiency III-V photo-catalysts for solar hydrogen production

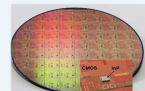
## Photovoltaics



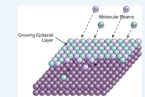
Bandgap engineering in III-Vs for high efficiency multijunction architectures

## III-V/Si co-integration

## Bonding strategies



## Monolithic integration



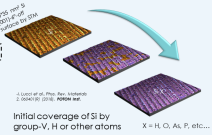
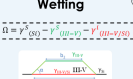
## III-V/Si crystal growth by MBE



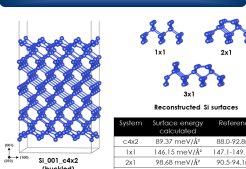
## Experiments



## Wetting

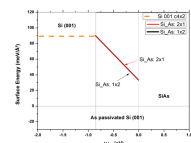
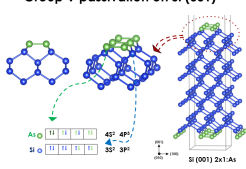


## Surface

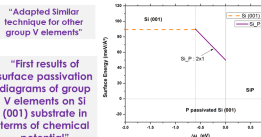
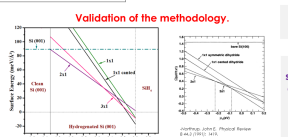
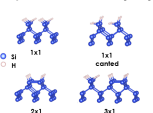


$$E_{\text{surf}} = E_{\text{bulk}} - (N_{\text{atoms}} \cdot E_{\text{atom}})$$

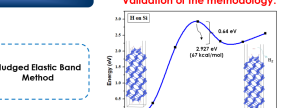
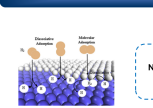
## Group V passivation on Si (001)



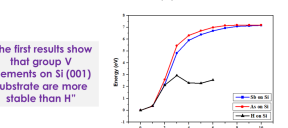
## H passivation on Si (001)



## Energy barrier



"As desorption on Si (001) behaves like molecular adsorption not dissociative adsorption for H on Si"



"The first results show that group V elements on Si (001) substrate are more stable than H"

## Conclusions

- Absolute surface energies of Si (001) surfaces with mono or sub-atomic layers of H and group V elements.
- Energy barrier calculation to study the desorption of different passivating elements from the Si surface.

## Prospects

- The surface and interface energies calculations for III-V/Si.
- The influence of dislocations and antiphase boundaries.

## Acknowledgements

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